Voltage Regulator - Ultra High Accuracy, Low Iq, Low Dropout, Enable

500 mA

The NCV8535 is a high performance, low dropout regulator. With accuracy of $\pm 0.9\%$ over line and load and ultra-low quiescent current and noise it encompasses all of the necessary features required by today's consumer electronics. This unique device is guaranteed to be stable without a minimum load current requirement and stable with any type of capacitor as small as 1.0 μF . The NCV8535 also comes equipped with sense and noise reduction pins to increase the overall utility of the device. The NCV8535 offers reverse bias protection.

Features

- High Accuracy Over Line and Load (±0.9% at 25°C)
- Ultra-Low Dropout Voltage at Full Load (260 mV typ.)
- No Minimum Output Current Required for Stability
- Low Noise (31 μVrms w/10 nF C_{nr} and 51 μVrms w/out C_{nr})
- Low Shutdown Current (0.07 μA)
- Reverse Bias Protected
- 2.9 V to 12 V Supply Range
- Thermal Shutdown Protection
- Current Limitation
- Requires Only 1.0 μF Output Capacitance for Stability
- Stable with Any Type of Capacitor (including MLCC)
- Available in 1.5 V, 1.8 V, 1.9 V, 2.5 V, 2.8 V, 2.85 V, 3.0 V, 3.3 V, 3.5 V, 5.0 V and Adjustable Output Voltages
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

Applications

- PCMCIA Card
- Cellular Phones
- Camcoders and Cameras
- Networking Systems, DSL/Cable Modems
- Cable Set-Top Box
- MP3/CD Players
- DSP Supply
- Displays and Monitors



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DFN10 CASE 485C DFNW10 CASE 507AM

PIN CONFIGURATION

Fixed Version	Adj Version
Pin 1, 2. Vout	Pin 1, 2. Vout
3. Sense	3. Adj
4. GND	4. GND
5, 6. NC	5, 6. NC
7. NR	7. NR
8. SD	8. <u>SD</u>
9, 10. V _{in}	9, 10. V _{in}

MARKING DIAGRAM





V8535 = Specific Device Code L8535 = Specific Device Code

xxx = ADJ, 150, 180, 190, 250, 280, 285, 300, 330, 350, 500

A = Assembly Location

= Wafer I of

= Wafer Lot = Year

W = Work Week
■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 21 of this data sheet.

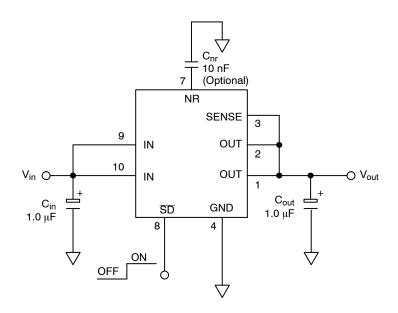


Figure 1. Typical Fixed Version Application Schematic

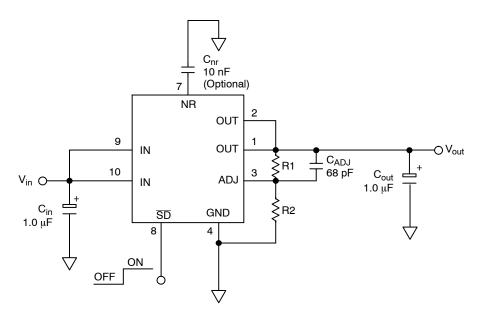


Figure 2. Typical Adjustable Version Application Schematic

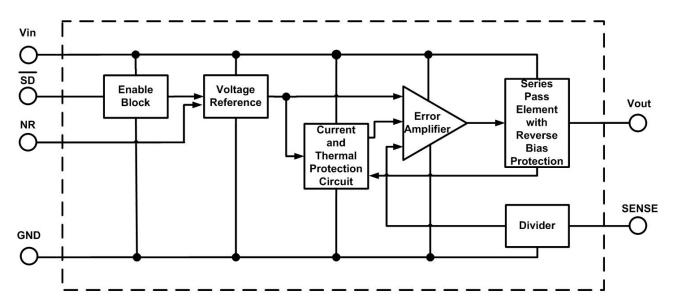


Figure 3. Block Diagram, Fixed Output Version

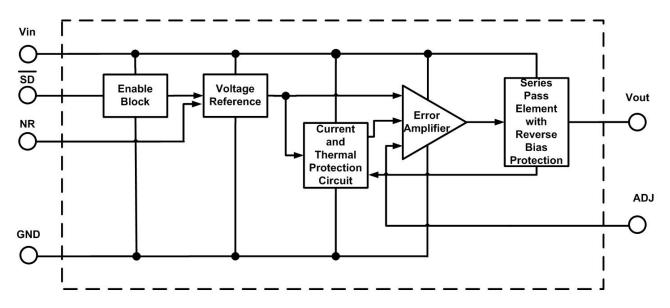


Figure 4. Block Diagram, Adjustable Output Version

PIN FUNCTION DESCRIPTION

Pin No.	Pin Name	Description				
FIXED VER	SION					
1, 2	V _{out}	Regulated output voltage. Bypass to ground with $C_{out} \geq 1.0~\mu F$.				
3	SENSE	For output voltage sensing, connect to Pins 1 and 2.				
4	GND	Power Supply Ground				
7	NR	Noise Reduction Pin. This is an optional pin used to further reduce noise.				
8	SD	Shutdown pin. When not in use, this pin should be connected to the input pin.				
9, 10	V _{in}	Power Supply Input Voltage				
5, 6	NC	Not Connected				
EPAD	EPAD	Exposed thermal pad should be connected to ground.				

ADJUSTABLE VERSION

1, 2	V _{out}	Regulated output voltage. Bypass to ground with $C_{out} \geq 1.0~\mu F$.
3	Adj	Adjustable pin; reference voltage = 1.25 V.
4	GND	Power Supply Ground
7	NR	Noise Reduction Pin. This is an optional pin used to further reduce noise.
8	SD	Shutdown pin. When not in use, this pin should be connected to the input pin.
9, 10	V _{in}	Power Supply Input Voltage
5, 6	NC	Not Connected
EPAD	EPAD	Exposed thermal pad should be connected to ground.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage	V _{in}	-0.3 to +16	V
Output Voltage	V _{out}	-0.3 to V _{in} +0.3 or 10 V*	V
Shutdown Pin Voltage	V_{sh}	-0.3 to +16	V
Junction Temperature Range	T_J	-40 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: This device series contains ESD protection and exceeds the following tests:

Human Body Model (HBM) tested per AEC-Q100-002 (EIA/JESD22-A114)

Machine Model (MM) tested per AEC-Q100-003 (EIA/JESD22-A115)

Charged Device Model (CDM) tested per EIA/JESD22-C101

THERMAL CHARACTERISTICS

	Test Conditions	(Typical Value)	
Characteristic	Min Pad Board (Note 1)	1" Pad Board (Note 1)	Unit
Junction-to-Air, θJA	215	66	°C/W
Junction-to-Pin, ψJL2	55	17	°C/W

^{1.} As mounted on a 35 x 35 x 1.5 mm FR4 Substrate, with a single layer of a specified copper area of 2 oz (0.07 mm thick) copper traces and heat spreading area. JEDEC 51 specifications for a low and high conductivity test board recommend a 2 oz copper thickness. Test conditions are under natural convection or zero air flow.

^{*}Which ever is less. Reverse bias protection feature valid only if $V_{out} - V_{in} \le 7 \text{ V}$.

ELECTRICAL CHARACTERISTICS - 5.0 V

(V_{out} = 5.0 V typical, V_{in} = 5.4 V, T_A = -40°C to +85°C, unless otherwise noted, Note 2.)

V _{out}	-0.9%			
	4.955	5.0	+0.9% 5.045	V
V _{out}	-1.4% 4.930	5.0	+1.4% 5.070	٧
V _{out}	-1.5% 4.925	5.0	+1.5% 5.075	V
Line _{Reg}		0.04		mV/V
Load _{Reg}		0.04		mV/mA
V _{DO}			340 230 110 10	mV
lpk	500	700	830	mA
I _{sc}			930	mA
TJ		160		°C
I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
		-	500	μΑ
I _{GNDsh}		0.07	1.0	μА
V _{noise}		93 58		μVrms μVrms
	2.0		0.4	V
I _{SD}		0.07	1.0	μА
I _{OSD}		0.07	1.0	μА
I _{OUTR}		10		μΑ
	Vout LineReg LoadReg VDO Ipk Isc TJ IGND IGNDsh Vnoise ISD IOSD IOUTR	4.930 Vout	Vout -1.5% 5.0	Vout

Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 3.5 V

(V_{out} = 3.5 V typical, V_{in} = 3.9 V, T_{A} = -40°C to +85°C, unless otherwise noted, Note 4.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) $V_{in} = 3.9 \text{ V to } 7.5 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 25^{\circ}\text{C}$	V _{out}	-0.9% 3.469	3.5	+0.9% 3.532	V
Output Voltage (Accuracy) $V_{in} = 3.9 \text{ V to } 7.5 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}$	V _{out}	-1.4% 3.451	3.5	+1.4% 3.549	V
Output Voltage (Accuracy) $V_{in} = 3.9 \text{ V to } 7.5 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$	V _{out}	-1.5% 3.448	3.5	+1.5% 3.553	V
Line Regulation $V_{in} = 3.9 \text{ V to } 12 \text{ V, } I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation $V_{in} = 3.9 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA}$	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA I _{load} = 300 mA I _{load} = 50 mA I _{load} = 0.1 mA	V _{DO}			340 230 110 10	mV
Peak Output Current (See Figure 16)	lpk	500	700	800	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation I _{load} = 500 mA (Note 5) I _{load} = 300 mA I _{load} = 50 mA I _{load} = 0.1 mA	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 3.4 \text{ V}$, $I_{load} = 0.1 \text{ mA}$			_	500	μΑ
In Shutdown $S_D = 0 \text{ V}$	I _{GNDsh}		0.07	1.0	μΑ
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF	V _{noise}		68 47		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S_D Input Current, V_{SD} = 0 V to 0.4 V or V_{SD} = 2.0 V to V_{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μΑ
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out_forced} = 3.5 V)	l _{OUTR}		10		μА

 ^{4.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 5. T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 3.3 V

(V_{out} = 3.3 V typical, V_{in} = 3.7 V, T_A = -40°C to +85°C, unless otherwise noted, Note 6.)

V _{out} V _{out}	-0.9% 3.270 -1.4% 3.254	3.3	+0.9% 3.330	V
		3.3		1
V _{out}			+1.4% 3.346	٧
	-1.5% 3.250	3.3	+1.5% 3.350	V
_ine _{Reg}		0.04		mV/V
oad _{Reg}		0.04		mV/mA
V _{DO}			340 230 110 10	mV
lpk	500	700	800	mA
I _{sc}			900	mA
TJ		160		°C
I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
		-	500	μΑ
I _{GNDsh}		0.07	1.0	μΑ
V _{noise}		69 46		μVrms μVrms
	2.0		0.4	V
I _{SD}		0.07	1.0	μΑ
I _{OSD}		0.07	1.0	μΑ
I _{OUTR}		10		μА
I (Dad _{Reg} VDO Ipk Isc TJ IGND GNDsh Vnoise ISD IOSD OUTR	ineReg padReg VDO Ipk 500 Isc TJ IGND GNDsh Vnoise 2.0 ISD IOSD OUTR	ineReg 0.04 DadReg 0.04 VDO 0.04 Ipk 500 700 Isc 7J 160 IGND 9.0 4.6 0.8 GINDsh 0.07 Vnoise 69 46 2.0 ISD 0.07 IOSD 0.07 OUTR 10	ineReg

 ^{6.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 7. T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 3.0 V

(V_{out} = 3.0 V typical, V_{in} = 3.4 V, T_A = -40°C to +85°C, unless otherwise noted, Note 8.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) V_{in} = 3.4 V to 7.0 V, I_{load} = 0.1 mA to 500 mA, T_A = 25°C	V _{out}	-0.9% 2.973	3.0	+0.9% 3.027	V
Output Voltage (Accuracy) $V_{in} = 3.4 \text{ V to } 7.0 \text{ V}, \ I_{load} = 0.1 \text{ mA to } 500 \text{ mA}, \ T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}$	V _{out}	-1.4% 2.958	3.0	+1.4% 3.042	V
Output Voltage (Accuracy) V_{in} = 3.4 V to 7.0 V, I_{load} = 0.1 mA to 500 mA, T_A = -40°C to +125°C	V _{out}	-1.5% 2.955	3.0	+1.5% 3.045	V
Line Regulation $V_{in} = 3.4 \text{ V to } 12 \text{ V}, I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation V _{in} = 3.4 V, I _{load} = 0.1 mA to 500 mA	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) $I_{load} = 500 \text{ mA}$ $I_{load} = 300 \text{ mA}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 50 \text{ mA}$	V _{DO}			340 230 110 10	mV
Peak Output Current (See Figure 16)	lpk	500	700	800	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation $I_{load} = 500 \text{ mA (Note 9)}$ $I_{load} = 300 \text{ mA}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 0.1 \text{ mA}$	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.9 \text{ V}, I_{load} = 0.1 \text{ mA}$			_	500	μА
In Shutdown S _D = 0 V	I _{GNDsh}		0.07	1.0	μΑ
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μ F C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μ F	V _{noise}		56 37		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S_D Input Current, V_{SD} = 0 V to 0.4 V or V_{SD} = 2.0 V to V_{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μА
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out_forced} = 3.0 V)	loutr		10		μΑ

Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 2.85 V

(V_{out} = 2.85 V typical, V_{in} = 3.25 V, T_A = -40°C to +85°C, unless otherwise noted, Note 10)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) $V_{in} = 3.25 \text{ V}$ to 6.85 V, $I_{load} = 0.1 \text{ mA}$ to 500 mA, $T_A = 25^{\circ}\text{C}$	V _{out}	-0.9% 2.824	2.85	+0.9% 2.876	٧
Output Voltage (Accuracy) $V_{in} = 3.25 \text{ V to } 6.85 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}$	V _{out}	-1.4% 2.810	2.85	+1.4% 2.890	V
Output Voltage (Accuracy) (Note 11) $V_{in}=3.25~V~to~6.85~V,~I_{load}=0.1~mA~to~500~mA,~T_{A}=-40^{\circ}C~to~+125^{\circ}C$	V _{out}	-1.5% 2.807	2.85	+1.5% 2.893	V
Line Regulation $V_{in} = 3.25 \text{ V to } 12 \text{ V}, \ I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation $V_{in} = 3.25 \text{ V}, I_{load} = 0.1 \text{ mA to } 500 \text{ mA}$	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA I _{load} = 300 mA I _{load} = 50 mA I _{load} = 0.1mA	V _{DO}			340 230 110 10	mV
Peak Output Current (See Figure 16)	I _{pk}	500	700	800	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation $I_{load} = 500 \text{ mA (Note 12)}$ $I_{load} = 300 \text{ mA}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 0.1 \text{ mA}$	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.75 \text{ V}$, $I_{load} = 0.1 \text{ mA}$			-	500	μΑ
In Shutdown $S_D = 0 \text{ V}$	I _{GNDsh}		0.07	1.0	μΑ
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF	V _{noise}		61 40		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S_D Input Current, V_{SD} = 0 V to 0.4 V or V_{SD} = 2.0 V to V_{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μА
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out_forced} = 2.85 V)	I _{OUTR}		10		μА

^{10.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

11. For output current capability for T_A < 0°C, please refer to Figure 18.

12. T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 2.8 V

(V_{out} = 2.8 V typical, V_{in} = 3.2 V, T_A = -40°C to +85°C, unless otherwise noted, Note 13.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) $V_{in} = 3.2 \text{ V to } 6.8 \text{ V, I}_{load} = 0.1 \text{ mA to } 500 \text{ mA, T}_A = 25^{\circ}\text{C}$	V _{out}	-0.9% 2.774	2.8	+0.9% 2.826	V
Output Voltage (Accuracy) $V_{in} = 3.2 \text{ V to } 6.8 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}$	V _{out}	-1.4% 2.760	2.8	+1.4% 2.840	V
Output Voltage (Accuracy) (Note 14) $V_{in} = 3.2 \text{ V to } 6.8 \text{ V, I}_{load} = 0.1 \text{ mA to } 500 \text{ mA, T}_{A} = -40^{\circ}\text{C to } +125^{\circ}\text{C}$	V _{out}	-1.5% 2.758	2.8	+1.5% 2.842	V
Line Regulation $V_{in} = 3.2 \text{ V to } 12 \text{ V}, I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation $V_{in} = 3.2 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA}$	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA I _{load} = 300 mA I _{load} = 50 mA I _{load} = 0.1mA	V _{DO}			340 230 110 10	mV
Peak Output Current (See Figure 16)	I _{pk}	500	700	800	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation $I_{load} = 500 \text{ mA (Note 15)}$ $I_{load} = 300 \text{ mA (Note 15)}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 0.1 \text{ mA}$	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.7 \text{ V}, I_{load} = 0.1 \text{ mA}$			-	500	μΑ
In Shutdown $S_D = 0 \text{ V}$	I _{GNDsh}		0.07	1.0	μΑ
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF	V _{noise}		52 36		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S_D Input Current, V_{SD} = 0 V to 0.4 V or V_{SD} = 2.0 V to V_{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μΑ
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out_forced} = 2.8 V)	loutr		10		μА

^{13.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

14. For output current capability for T_A < 0°C, please refer to Figure 19.

15. T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 2.5 V

(V_{out} = 2.5 V typical, V_{in} = 2.9 V, T_A = -40°C to +85°C, unless otherwise noted, Note 16.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) $V_{in} = 2.9 \text{ V to } 6.5 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 25 ^{\circ}\text{C}$	V _{out}	-0.9% 2.477	2.5	+0.9% 2.523	V
Output Voltage (Accuracy) $V_{in} = 2.9 \text{ V to } 6.5 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}$	V _{out}	-1.4% 2.465	2.5	+1.4% 2.535	V
Output Voltage (Accuracy), (Note 17) $V_{in}=2.9~V~to~6.5~V,~I_{load}=0.1~mA~to~500~mA,~T_{A}=-40^{\circ}C~to~+125^{\circ}C$	V _{out}	-1.5% 2.462	2.5	+1.5% 2.538	V
Line Regulation $V_{in} = 2.9 \text{ V to } 12 \text{ V, } I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation $V_{in} = 2.9 \text{ V}, I_{load} = 0.1 \text{ mA to } 500 \text{ mA}$	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA (Note 18) I _{load} = 300 mA (Note 18) I _{load} = 50 mA I _{load} = 0.1mA	V _{DO}			340 230 110 10	mV
Peak Output Current (See Figure 16)	I _{pk}	500	700	800	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation $I_{load} = 500 \text{ mA (Note 18)}$ $I_{load} = 300 \text{ mA (Note 18)}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 0.1 \text{ mA}$	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.4 \text{ V}, I_{load} = 0.1 \text{ mA}$				500	μΑ
In Shutdown $S_D = 0 \text{ V}$	I _{GNDsh}		0.07	1.0	μΑ
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF	V _{noise}		56 35		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S_D Input Current, V_{SD} = 0 V to 0.4 V or V_{SD} = 2.0 V to V_{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, Vout = 0 V	I _{OSD}		0.07	1.0	μΑ
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out forced} = 2.5 V)	I _{OUTR}		10		μΑ

^{16.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

17. For output current capability for T_A < 0°C, please refer to Figure 20.

18. T_A must be greater than 0°C.

ELECTRICAL CHARACTERISTICS - 1.9 V

(V_{out} = 1.9 V typical, V_{in} = 2.9 V, T_A = -40°C to +85°C, unless otherwise noted, Note 19.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) V_{in} = 2.9 V to 5.9 V, I_{load} = 0.1 mA to 500 mA, T_A = 25°C	V _{out}	-0.9% 1.883	1.9	+0.9% 1.917	V
Output Voltage (Accuracy) $V_{in} = 2.9 \text{ V to } 5.9 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}$	V _{out}	-1.4% 1.873	1.9	+1.4% 1.927	٧
Output Voltage (Accuracy), (Note 20) $V_{in}=2.9~V~to~5.9~V,~I_{load}=0.1~mA~to~500~mA,~T_{A}=-40^{\circ}C~to~+125^{\circ}C$	V _{out}	-1.5% 1.872	1.9	+1.5% 1.929	V
Line Regulation $V_{in} = 2.9 \text{ V to } 12 \text{ V, } I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation $V_{in} = 2.9 \text{ V}, I_{load} = 0.1 \text{ mA to } 500 \text{ mA}$	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA (Notes 21, 22) I _{load} = 300 mA (Notes 21, 22) I _{load} = 50 mA (Notes 21, 22)	V _{DO}		367 156 90	1030 1030 1030	mV
Peak Output Current (See Figure 16)	I _{pk}	500	700	800	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation I _{load} = 500 mA (Note 21) I _{load} = 300 mA (Note 21) I _{load} = 50 mA I _{load} = 0.1 mA	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.2 \text{ V}, I_{load} = 0.1 \text{ mA}$				500	μΑ
In Shutdown S _D = 0 V	I _{GNDsh}		0.07	1.0	μА
Output Noise $C_{nr}=0 \text{ nF, } I_{load}=500 \text{ mA, } f=10 \text{ Hz to } 100 \text{ kHz, } C_{out}=10 \mu\text{F} \\ C_{nr}=10 \text{ nF, } I_{load}=500 \text{ mA, } f=10 \text{ Hz to } 100 \text{ kHz, } C_{out}=10 \mu\text{F}$	V _{noise}		53 33		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S_D Input Current, V_{SD} = 0 V to 0.4 V or V_{SD} = 2.0 V to V_{in}	I _{SD}		0.07	1.0	μА
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μΑ
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out_forced} = 1.9 V)	l _{outr}		10		μА

^{19.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

20. For output current capability for T_A < 0°C, please refer to Figure 21.

21. T_A must be greater than 0°C.

22. Maximum dropout voltage is limited by minimum input voltage V_{in} = 2.9 V recommended for guaranteed operation.

ELECTRICAL CHARACTERISTICS - 1.8 V

(V_{out} = 1.8 V typical, V_{in} = 2.9 V, T_A = -40°C to +85°C, unless otherwise noted, Note 23.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) V_{in} = 2.9 V to 5.8 V, I_{load} = 0.1 mA to 500 mA, T_A = 25°C	V _{out}	-0.9% 1.783	1.8	+0.9% 1.817	V
Output Voltage (Accuracy) V_{in} = 2.9 V to 5.8 V, I_{load} = 0.1 mA to 500 mA, T_A = 0°C to +85°C	V _{out}	-1.4% 1.774	1.8	+1.4% 1.826	V
Output Voltage (Accuracy), (Note 24) V_{in} = 2.9 V to 5.8 V, I_{load} = 0.1 mA to 500 mA, T_A = -40°C to +125°C	V _{out}	-1.5% 1.773	1.8	+1.5% 1.827	٧
Line Regulation $V_{in} = 2.9 \text{ V to } 12 \text{ V}, I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation V _{in} = 2.9 V, I _{load} = 0.1 mA to 500 mA	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA (Notes 25, 26) I _{load} = 300 mA (Notes 25, 26) I _{load} = 50 mA (Notes 25, 26)	V _{DO}		620 230 95	1130 1130 1130	mV
Peak Output Current (See Figure 16)	I _{pk}	500	700	830	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation I _{load} = 500 mA (Note 25) I _{load} = 300 mA (Note 25) I _{load} = 50 mA I _{load} = 0.1 mA	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.2 \text{ V}$, $I_{load} = 0.1 \text{ mA}$				500	μΑ
In Shutdown $S_D = 0 \text{ V}$	I _{GNDsh}		0.07	1.0	μА
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF	V _{noise}		52 33		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S _D Input Current, V _{SD} = 0 V to 0.4 V or V _{SD} = 2.0 V to V _{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μΑ
Reverse Bias Protection, Current Flowing from the Output Pin to GND (V _{in} = 0 V, V _{out_forced} = 1.8 V)	loutr		10		μА

^{23.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

24. For output current capability for T_A < 0°C, please refer to Figure 21.

25. T_A must be greater than 0°C.

26. Maximum dropout voltage is limited by minimum input voltage V_{in} = 2.9 V recommended for guaranteed operation.

ELECTRICAL CHARACTERISTICS - 1.5 V

(V_{out} = 1.5 V typical, V_{in} = 2.9 V, T_A = -40°C to +85°C, unless otherwise noted, Note 27.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage (Accuracy) $V_{in} = 2.9 \text{ V to } 5.5 \text{ V, } I_{load} = 0.1 \text{ mA to } 500 \text{ mA, } T_A = 25^{\circ}\text{C}$	V _{out}	-0.9% 1.486	1.5	+0.9% 1.514	V
Output Voltage (Accuracy) V_{in} = 2.9 V to 5.5 V, I_{load} = 0.1 mA to 500 mA, T_A = 0°C to +85°C	V _{out}	-1.4% 1.479	1.5	+1.4% 1.521	V
Output Voltage (Accuracy), (Note 28) V_{in} = 2.9 V to 5.5 V, I_{load} = 0.1 mA to 500 mA, T_A = -40°C to +125°C	V _{out}	-1.5% 1.477	1.5	+1.5% 1.523	V
Line Regulation $V_{in} = 2.9 \text{ V to } 12 \text{ V}, I_{load} = 0.1 \text{ mA}$	Line _{Reg}		0.04		mV/V
Load Regulation V _{in} = 2.9 V, I _{load} = 0.1 mA to 500 mA	Load _{Reg}		0.04		mV/mA
Dropout Voltage (See App Note) I _{load} = 500 mA (Notes 29, 30) I _{load} = 300 mA (Notes 29, 30) I _{load} = 50 mA (Notes 29, 30)	V _{DO}		940 500 350	1430 1430 1430	mV
Peak Output Current (See Figure 16)	I _{pk}	500	700	860	mA
Short Output Current (See Figure 16)	I _{sc}			900	mA
Thermal Shutdown	TJ		160		°C
Ground Current In Regulation $I_{load} = 500 \text{ mA (Note 29)}$ $I_{load} = 300 \text{ mA (Note 29)}$ $I_{load} = 50 \text{ mA}$ $I_{load} = 0.1 \text{ mA}$	I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
In Dropout $V_{in} = 2.2 \text{ V}, I_{load} = 0.1 \text{ mA}$				500	μΑ
In Shutdown $S_D = 0 \text{ V}$	I _{GNDsh}		0.07	1.0	μΑ
Output Noise C_{nr} = 0 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF C_{nr} = 10 nF, I_{load} = 500 mA, f = 10 Hz to 100 kHz, C_{out} = 10 μF	V _{noise}		51 31		μVrms μVrms
Shutdown Threshold Voltage ON Threshold Voltage OFF		2.0		0.4	V
S _D Input Current, V _{SD} = 0 V to 0.4 V or V _{SD} = 2.0 V to V _{in}	I _{SD}		0.07	1.0	μΑ
Output Current In Shutdown Mode, V _{out} = 0 V	I _{OSD}		0.07	1.0	μА
Reverse Bias Protection, Current Flowing from the Output Pin to GND $(V_{in} = 0 \text{ V}, V_{out_forced} = 1.5 \text{ V})$	loutr		10		μΑ

^{27.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

28. For output current capability for T_A < 0°C, please refer to Figure 22.

29. T_A must be greater than 0°C.

30. Maximum dropout voltage is limited by minimum input voltage V_{in} = 2.9 V recommended for guaranteed operation.

ELECTRICAL CHARACTERISTICS – Adjustable

(V_{out} = 1.25 V typical, V_{in} = 2.9 V, T_A = -40°C to +85°C, unless otherwise noted, Note 31)

V _{ref}	-0.9% 1.239	1.25	+0.9%	V
			1.261	\ \ \
V_{ref}	-1.4% 1.233	1.25	+1.4% 1.268	V
V_{ref}	-1.5% 1.231	1.25	+1.5% 1.269	V
Line _{Reg}		0.04		mV/V
Load _{Reg}		0.04		mV/mA
V _{DO}			340 230 110 10	mV
lpk	500	700	860	mA
I _{sc}			900 990	mA
TJ		160		°C
I _{GND}		9.0 4.6 0.8	14 7.5 2.5 190	mA μA
		_	500	μΑ
I _{GNDsh}		0.07	1.0	μΑ
V _{noise}		38 26		μVrms μVrms
	2.0		0.4	V
I _{SD}		0.07	1.0 5.0	μА
I _{OSD}		0.07	1.0	μΑ
l _{OUTR}		1.0		μΑ
	Line _{Reg} Load _{Reg} V _{DO} Ipk I _{sc} T _J I _{GND} I _{GNDsh} V _{noise} I _{SD} I _{OSD}	Vref	Vref -1.5% 1.231 1.25 Line _{Reg} 0.04 Load _{Reg} 0.04 VDO 0.04 Ipk 500 700 I _{SC} 0.00 I _{GND} 9.0 4.6 0.8 - 4.6 0.8 - - - - I _{GNDsh} 0.07 0.07 V _{noise} 38 26 2.0 I _{SD} 0.07 I _{OSD} 0.07	Vref -1.5% 1.25 +1.5% LineReg 0.04 -1.269 LoadReg 0.04 -1.269 VDO 340 -230 LoadReg 0.04 -1.269 VDO 340 -230 LID -1.0 -1.0 LID -1.0

^{31.} Performance guaranteed over the operating temperature range by design and/or characterization, production tested at T_J = T_A = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

32. For output current capability for T_A < 0°C, please refer to Figures 18 to 22.

33. T_A must be greater than 0°C.

34. Reverse bias protection feature valid only if V_{out} − V_{in} ≤ 7 V.

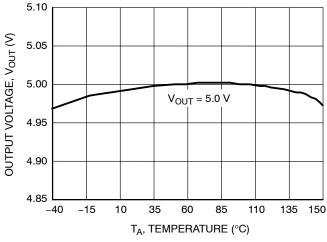


Figure 5. Output Voltage vs. Temperature 5.0 V Version

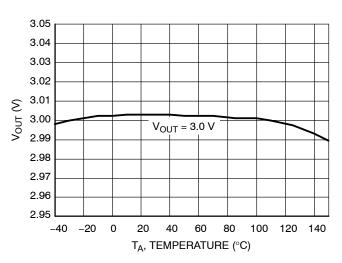


Figure 6. Output Voltage vs. Temperature 3.0 V Version

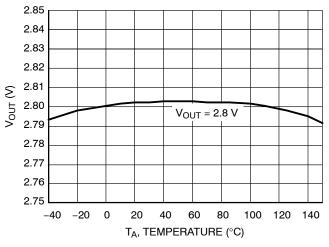


Figure 7. Output Voltage vs. Temperature 2.8 V Version

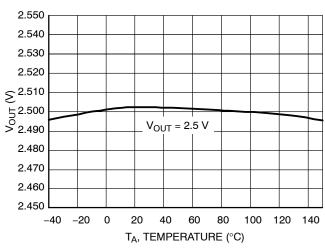


Figure 8. Output Voltage vs. Temperature 2.5 V Version

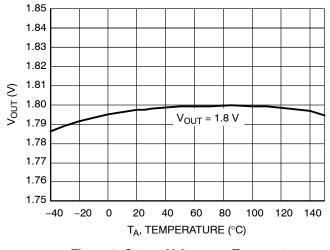


Figure 9. Output Voltage vs. Temperature 1.8 V Version

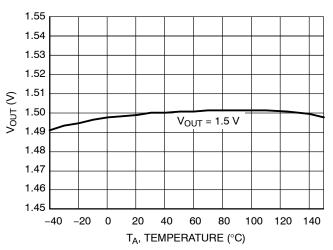


Figure 10. Output Voltage vs. Temperature 1.5 V Version

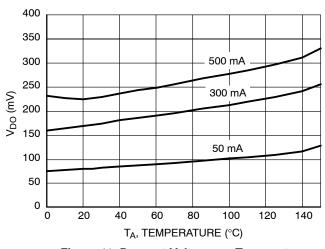


Figure 11. Dropout Voltage vs. Temperature 2.8 V Version

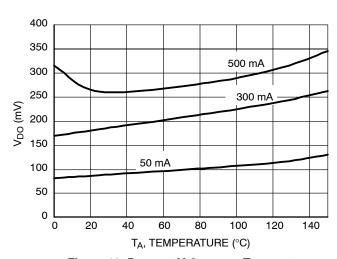


Figure 12. Dropout Voltage vs. Temperature 2.5 V Version

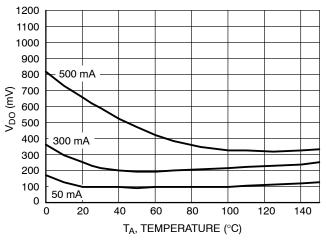


Figure 13. Dropout Voltage vs. Temperature 1.8 V Version

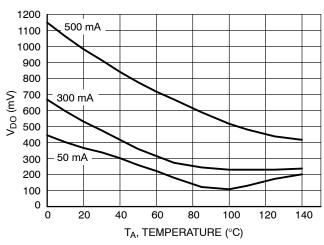


Figure 14. Dropout Voltage vs. Temperature 1.5 V Version

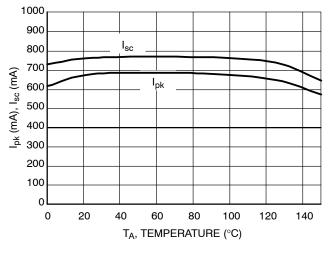


Figure 15. Peak and Short Current vs. Temperature

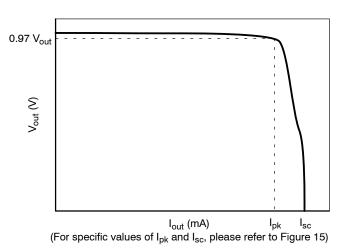


Figure 16. Output Voltage vs. Output Current

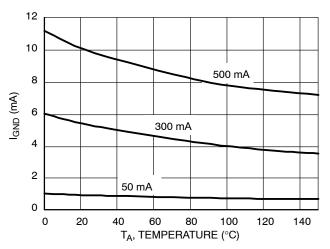


Figure 17. Ground Current vs. Temperature

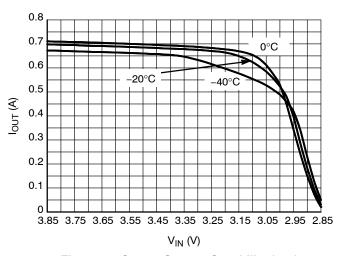


Figure 18. Output Current Capability for the 2.85 V Version

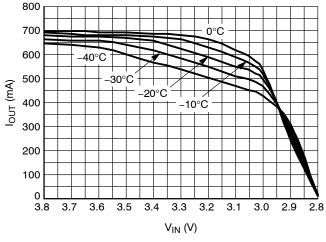


Figure 19. Output Current Capability for the 2.8 V Version

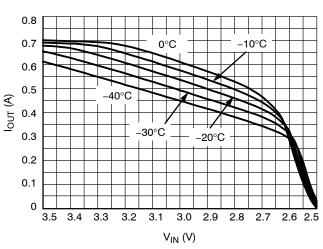


Figure 20. Output Current Capability for the 2.5 V Version

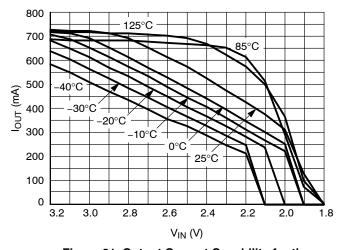


Figure 21. Output Current Capability for the 1.8 V Version

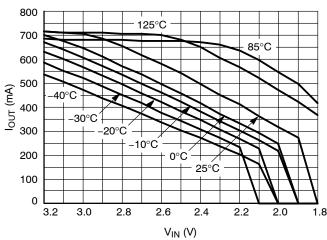


Figure 22. Output Current Capability for the 1.5 V Version

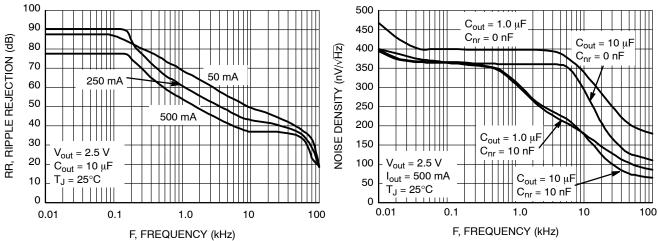


Figure 23. Ripple Rejection vs. Frequency

Figure 24. Output Noise Density

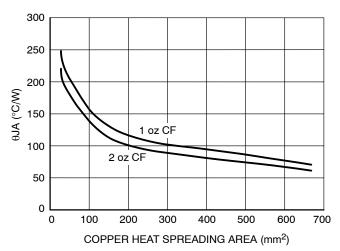
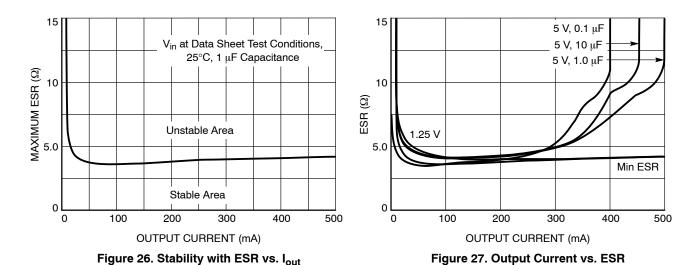


Figure 25. DFN 10 Self Heating Thermal Characteristic as a Function of Copper Area on the PCB



NOTE: Typical characteristics were measured with the same conditions as electrical characteristics.

APPLICATIONS INFORMATION

Reverse Bias Protection

Reverse bias is a condition caused when the input voltage goes to zero, but the output voltage is kept high either by a large output capacitor or another source in the application which feeds the output pin.

Normally in a bipolar LDO all the current will flow from the output pin to input pin through the PN junction with limited current capability and with the potential to destroy the IC.

Due to an improved architecture, the NCV8535 can withstand up to 7.0 V on the output pin with virtually no current flowing from output pin to input pin, and only negligible amount of current (tens of μA) flowing from the output pin to ground for infinite duration.

Input Capacitor

An input capacitor of at least 1.0 μ F, any type, is recommended to improve the transient response of the regulator and/or if the regulator is located more than a few inches from the power source. It will also reduce the circuit's sensitivity to the input line impedance at high frequencies. The capacitor should be mounted with the shortest possible track length directly across the regular's input terminals.

Output Capacitor

The NCV8535 remains stable with any type of capacitor as long as it fulfills its 1.0 μF requirement. There are no constraints on the minimum ESR and it will remain stable up to an ESR of 5.0 Ω . Larger capacitor values will improve the noise rejection and load transient response.

Noise Reduction Pin

Output noise can be greatly reduced by connecting a 10 nF capacitor (C_{nr}) between the noise reduction pin and ground (see Figure 1). In applications where very low noise is not required, the noise reduction pin can be left unconnected.

For the adjustable version, in addition to the $10 \text{ nF } C_{nr}$, a 68 pF capacitor connected in parallel with R1 (see Figure 2) is recommended to further reduce output noise and improve stability.

Adjustable Operation

The output voltage can be set by using a resistor divider as shown in Figure 2 with a range of 1.25 to 10 V. The appropriate resistor divider can be found by solving the equation below. The recommended current through the resistor divider is from 10 μA to 100 μA . This can be accomplished by selecting resistors in the $k\Omega$ range. As result, the $I_{adj}*R2$ becomes negligible in the equation and can be ignored.

$$V_{out} = 1.25 * \left(1 + \frac{R1}{R2}\right) + I_{adj} * R2$$
 (eq. 1)

Example:

For V_{out} = 2.9 V, can use R_1 = 36 k Ω and R_2 = 27 k Ω .

$$1.25 * \left(1 + \frac{36 \text{ k}\Omega}{27 \text{ k}\Omega}\right) = 2.91 \text{ V}$$
 (eq. 2)

Dropout Voltage

The voltage dropout is measured at 97% of the nominal output voltage.

No-Load Regulation Considerations

If there is no load at output of the regulator and ambient temperature is higher than $85^{\circ}\mathrm{C}$ leakage current flowing from input to output through pass transistor may cause increase of output voltage out of specification range up to input voltage level. To avoid this situation minimum load current of $100~\mu\mathrm{A}$ or higher is recommended if ambient temperature exceeds $85^{\circ}\mathrm{C}$.

Thermal Considerations

Internal thermal limiting circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. This feature provides protection from a catastrophic device failure due to accidental overheating. This protection feature is not intended to be used as a substitute to heat sinking. The maximum power that can be dissipated, can be calculated with the equation below:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$
 (eq. 3)

DEVICE ORDERING INFORMATION

Device*	Voltage Option	Marking Code	Package	Feature	Shipping [†]
NCV8535MNADJR2G	Adj.	V8535 ADJ			
NCV8535MN150R2G	1.5 V	V8535 150			
NCV8535MN180R2G	1.8 V	V8535 180			
NCV8535MN190R2G	1.9 V	V8535 190			3000 / Tape & Reel
NCV8535MN250R2G	2.5 V	V8535 250			
NCV8535MN280R2G	2.8 V	V8535 280	DFN10 (Pb-Free)	Non-Wettable Flank	
NCV8535MN285R2G	2.85 V	V8535 285	(* 2 * * * * * * * * * * * * * * * * * *		
NCV8535MN300R2G	3.0 V	V8535 300			
NCV8535MN330R2G	3.3 V	V8535 330			
NCV8535MN350R2G	3.5 V	V8535 350			
NCV8535MN500R2G	5.0 V	V8535 500			
NCV8535MLADJR2G	Adj.	L8535 ADJ			
NCV8535ML180R2G	1.8 V	L8535 180	DFN10	Wettable Flank SLP Process	
NCV8535ML250R2G	2.5 V	L8535 250	(Pb-Free)		3000 / Tape & Reel
NCV8535ML330R2G	3.3 V	L8535 330			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

Capable.

PIN 1

// 0.10 C

REFERENCE





В

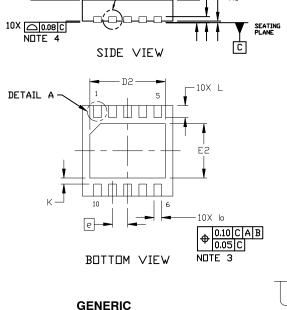
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DATE 16 DEC 2021

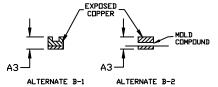
NOTES:

- DIMENSION AND TOLERANCING PER ASME Y14.5, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
- TERMINAL 6 MAY HAVE MOLD COMPOUND MATERIAL ALONG SIDE EDGE. MOLD FLASH MAY NOT EXCEED 30 MICRONS ONTO BOTTOM SURFACE OF TERMINAL.
- 6. FOR DEVICE OPN CONTAINING W OPTION, DETAIL A AND DETAIL B ALTERNATE CONSTRUCTIONS ARE NOT APPLICABLE. WETTABLE FLANK CONSTRUCTION IS DETAIL B AS SHOWN ON SIDE VIEW OF PACKAGE.

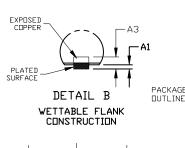


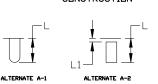
TOP VIEW

DETAIL B

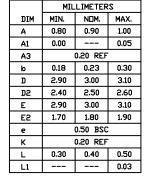


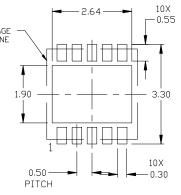
DETAIL B ALTERNATE CONSTRUCTION





DETAIL A ALTERNATE CONSTRUCTION





RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

XXXXX XXXXX ALYW.

MARKING DIAGRAM*

XXXXX = Specific Device Code = Assembly Location Α

Т = Wafer Lot Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DFN10, 3X3 MM, 0.5 MM P	ITCH	PAGE 1 OF 1		

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TOP VIEW

DETAIL B

SIDE VIEW

A1

С

A



PIN DNE -REFERENCE

// 0.10 C

NOTE 4

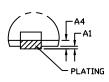
10X \(\sigma 0.08 \) C

DFNW10 3x3, 0.5P CASE 507AM ISSUE A

DATE 12 JUN 2018

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM THE TERMINAL TIP.
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



DETAIL B

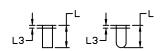


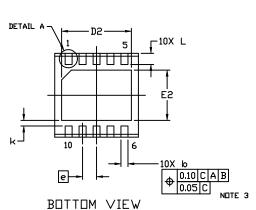


SECTION C-C

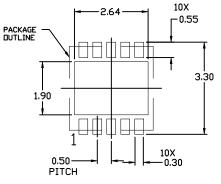
DIM	MIN.	N□M.	MAX.		
Α	0.80	0.90	1.00		
A1	0.00		0.05		
A3	0.20 REF				
Α4	0.10				
b	0.20	0.25	0.30		
D	2.85	3.00	3.15		
D2	2.40	2.50	2.60		
Ε	2.85	3.00	3.15		
E2	1.70	1.80	1.90		
е	0.50 BSC				
k	0.19 REF				
L	0.35	0.40	0.45		
L3		0.05	0.10		

MILLIMETERS





ALTERNATE CONSTRUCTION
DETAIL A



RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM

O XXXXX XXXXX ALYW= XXXXX = Specific Device Code A = Assembly Location

L = Wafer Lot
 Y = Year
 W = Work Week

SEATING PLANE

Ċ

■ = Pb-Free Package (Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DFNW10 3x3, 0.5P		PAGE 1 OF 1		

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